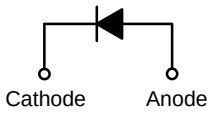
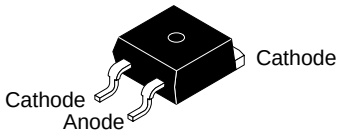
Silicon Carbide (SiC) Schottky Diode – EliteSiC, 30 A, 650 V, D2, D2PAK-2L

FFSB3065B-F085



Schottky Diode

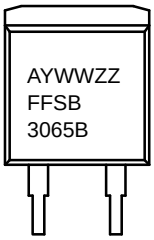


Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and ease of paralleling.

263−2Li)
CASE 418BK

MARKING DIAGRAM



A	= Assembly Plant Code
YWW	= Date Code (Year & Week)
ZZ	= Lot Code
FFSB3065B	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	650	V

TEST CIRCUIT AND WAVEFORMS

L = 0.5 mH
R < 0.1 Ω
V_{DD} = 50 V
EAVL = 1/2LI2 [$V_{R(AVL)}$ / ($V_{R(AVL)}$ − V_{DD})]
Q1 = IGBT (BV_{CES} > DUT $V_{R(AVL)}$)

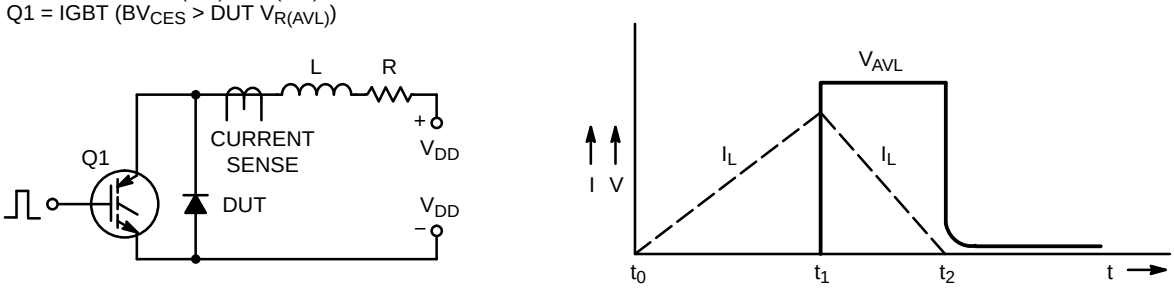


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

D²PAK2 (TO−263−2L)
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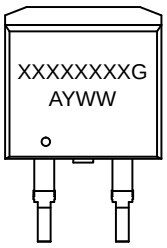
ISSUE O

DATE 02 AUG 2018

DETA

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.